

Features

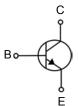
- Collector Current Capability Ic=0.2A
- Collector Emitter Voltage VcEo=40V

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)		
HMMBT3904WT1G	SOT-323	K2N	3000		



SOT-323



Maxmim Ratings (Ta=25 unless otherwise noted)

Parameter	Symbol	Rating	Unit		
Collector - Base Voltage	Vсво	60			
Collector - Emitter Voltage	VCEO	40	V		
Emitter - Base Voltage	VEBO	5			
Collector Current - Continuous	Ic	200	mA		
Collector Power Dissipation	Pc	200	mW		
Thermal Resistance From Junction To Ambient	Roja	625	°C/W		
Junction Temperature	TJ	150	$^{\circ}$ C		
Storage Temperature Range	Tstg	-55 to 150	C		

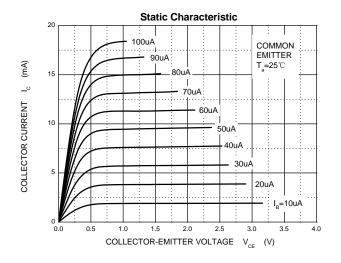
Electrcal Charcteristics (Ta=25 unless otherwise specified)

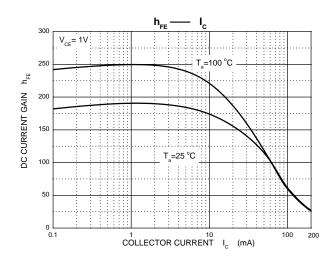
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector- base breakdown voltage	Vсво	Ic= 100 μA, IE= 0 (Note.1)	60			
Collector- emitter breakdown voltage	VCEO	Ic= 1 mA, I _B = 0 (Note.1)	40			V
Emitter - base breakdown voltage	VEBO	IE= 100 μ A, IC= 0 (Note.1)	5			
Collector-base cut-off current	Ісво	Vcb= 60 V , IE= 0 (Note.1)			60	
Collector- emitter cut-off current	ICEO	VcE= 40 V , IE= 0 (Note.1)			700	nA
Collector- emitter cut-off current	ICEX	VCE= 30 V ,VBE(off)= 3V			50	IIA
Emitter cut-off current	ІЕВО	VEB= 5V , IC=0			100	
Collector-emitter saturation voltage (Note.1)	VCE(sat)	Ic=10 mA, IB=1 mA			0.25	
Collector-entitler saturation voltage (Note.1)	V CE(Sai)	Ic=50 mA, Iв=5 mA			0.3	V
Base - emitter saturation voltage (Note.1)	VBE(sat)	Ic=10 mA, IB=1 mA			0.85	
base - eniliter saturation voltage (Note.1)	V BE(Sai)	Ic=50 mA, Iв=5 mA			0.95	
	hFE(1)	VcE= 1V, Ic= 100 uA	40			
DC current gain (Note.1)	hFE(2)	VCE= 1V, IC= 1 mA	70			
(Note.1)	hFE(3)	VCE= 1V, IC= 10 mA	100		300	
	hFE(4)	VcE= 1V, Ic= 50 mA	60			
Delay time	td	VCC=3V, VBE(off)=0.5V IC=10mA,			35	nS
Rise time	tr	IB1=1mA			35	
Storage time	ts	Voc. 2V to 40mA to 150 4mA			225	
Fall time	tf	Vcc=3V, Ic=10mA, IB1= IB2=1mA			75	
Collector input capacitance	Cib	VEB= 0.5V, IE= 0,f=1MHz			8	nE.
Collector output capacitance	Cob	VCB= 5V, IE= 0,f=1MHz			4	pF
Transition frequency	f⊤	VcE= 20V, Ic= 10mA,f=100MHz	300			MHz

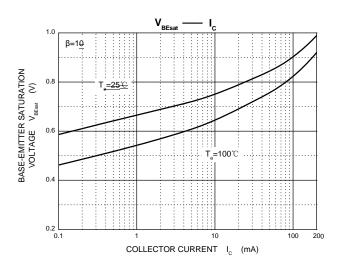
Note.1: Pulse test: pulse width \leq 300µs duty cycle \leq 2.0%.

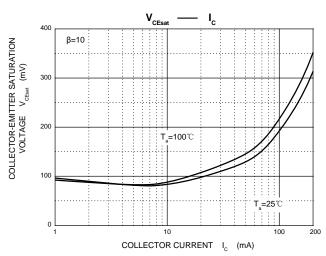


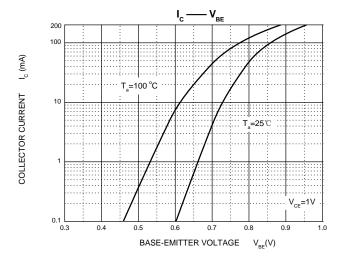
Typical Characteristics

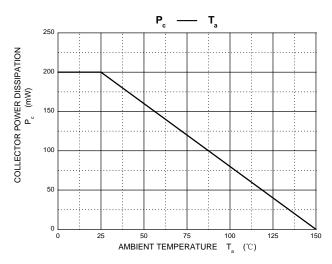






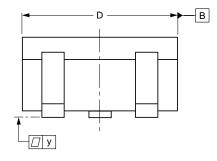


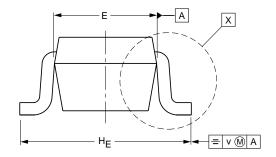


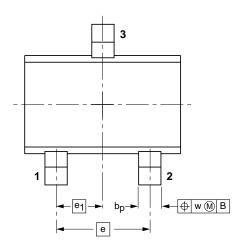


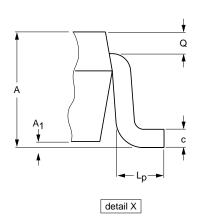


SOT-323 Package Outline Dimensions











DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

HMMBT3904WT1G NPN Plastic-Encapsulate Transistors

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